

RJL6020DPK

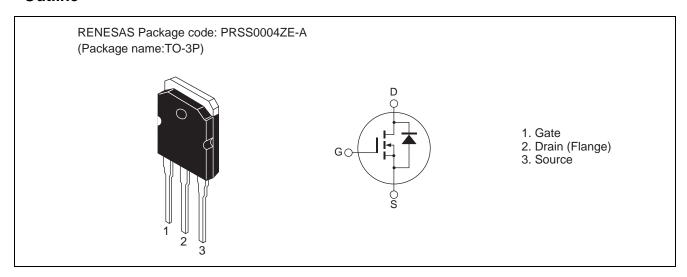
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1618-0300 Rev.3.00 Jan 22, 2010

Features

- Built-in fast recovery diode
- Low on-resistance $R_{DS(on)}=0.17~\Omega~typ.~(at~I_D=15~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	600	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	30	A
Drain peak current	I _{D (pulse)} Note1	90	A
Body-drain diode reverse drain current	I _{DR}	30	A
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	90	A
Avalanche current	I _{AP} Note3	8.5	A
Avalanche energy	E _{AR} Note3	3.9	mJ
Channel dissipation	Pch Note2	200	W
Channel to case thermal impedance	θch-c	0.625	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

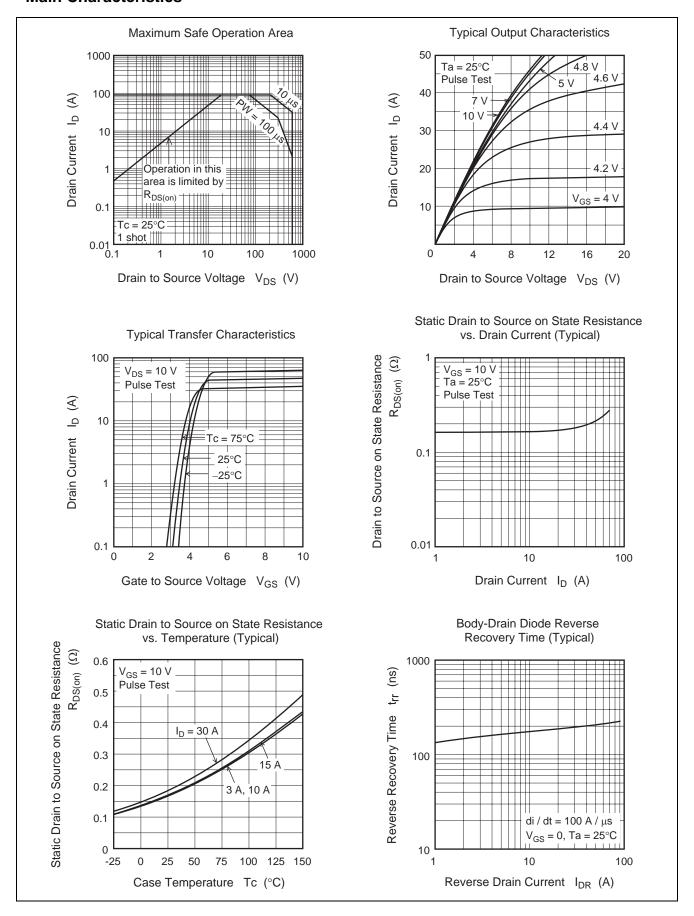
Electrical Characteristics

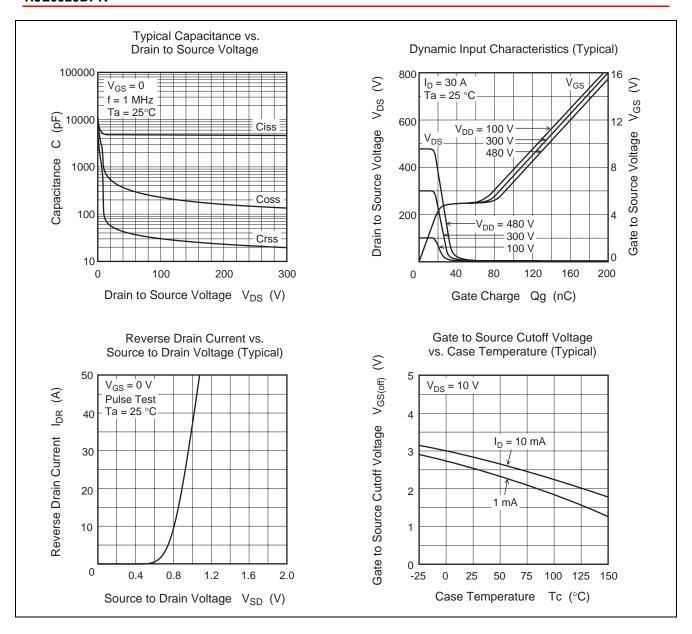
 $(Ta = 25^{\circ}C)$

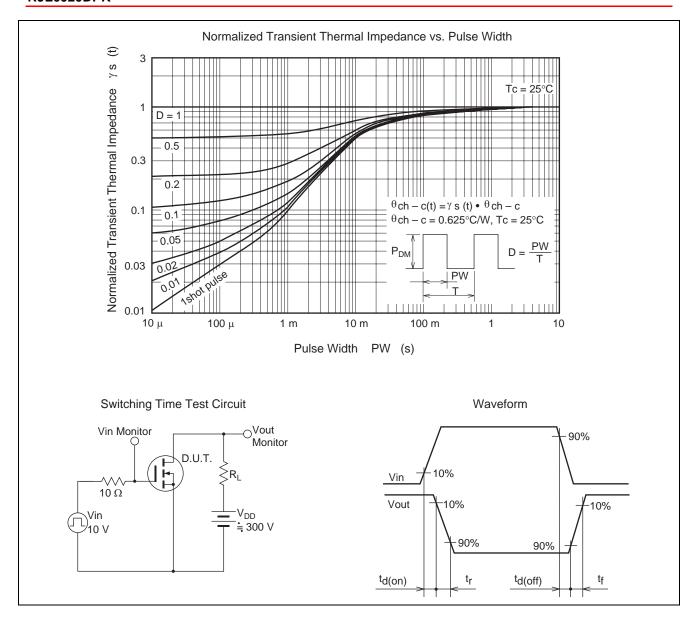
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	600		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Zero gate voltage drain current	I _{DSS}			10	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$	
Gate to source leak current	I _{GSS}		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	
Static drain to source on state resistance	R _{DS(on)}	_	0.17	0.21	Ω	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$	
Input capacitance	Ciss	_	4750	_	pF	V _{DS} = 25 V	
Output capacitance	Coss	_	465	_	pF	$V_{GS} = 0$	
Reverse transfer capacitance	Crss	_	53	_	pF	f = 1 MHz	
Turn-on delay time	t _{d(on)}	_	44	_	ns	I _D = 15 A	
Rise time	t _r	_	64	_	ns	$V_{GS} = 10 \text{ V}$ $R_L = 20 \Omega$	
Turn-off delay time	$t_{d(off)}$	_	206	_	ns		
Fall time	t _f	_	121	_	ns	$Rg = 10 \Omega$	
Total gate charge	Qg	_	130	_	nC	V _{DD} = 480 V	
Gate to source charge	Qgs	_	21	_	nC	V _{GS} = 10 V	
Gate to drain charge	Qgd	_	53	_	nC	I _D = 30 A	
Body-drain diode forward voltage	V_{DF}	_	0.96	1.60	V	$I_F = 30 \text{ A}, V_{GS} = 0^{\text{Note4}}$	
Body-drain diode reverse recovery time	t _{rr}	_	180	_	ns	$I_F = 30 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$	

Notes: 4. Pulse test

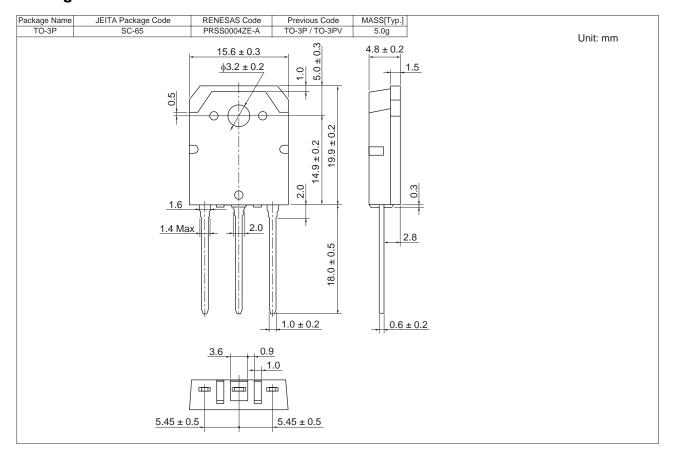
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container	
RJL6020DPK-00-T0	360 pcs	Box (Tube)	

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

 1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect of the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

 3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is a subject to change without any plan protein procedure is a subject to change without any plan protein procedure is an advantage of the procedure is a subject of the procedure is an advantage of the procedure is a subject of the procedure is a



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510